Characterization of pixel modules for the Phase-II upgrade of the ATLAS detector

18th Gentner Day, 28th October 2020

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Federal Ministry of Education and Research

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- ATLAS Inner Tracker Pixel - Outer Barrel Demonstrator
- Characterization of RD53A pixel modules using X-Ray Fluorescence
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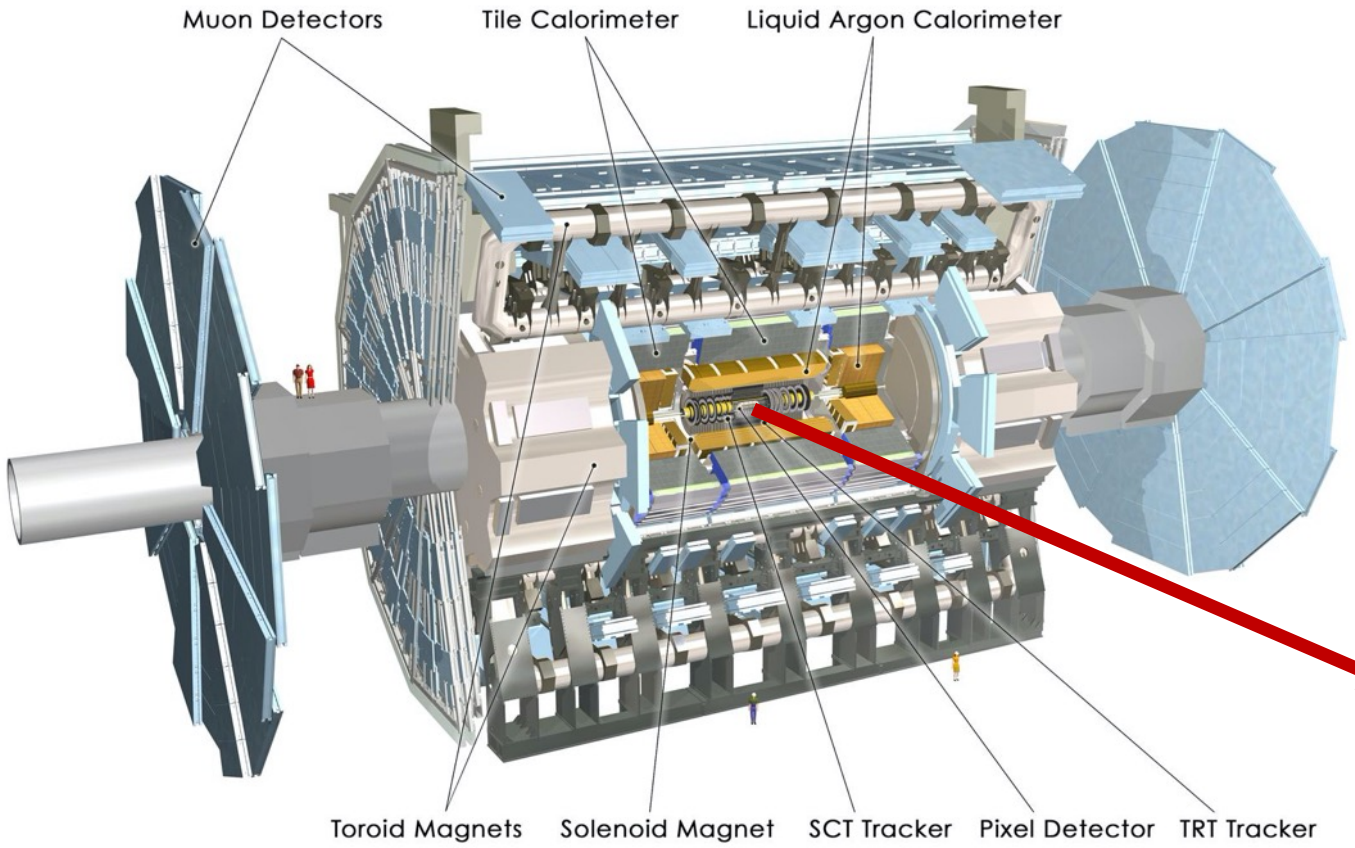
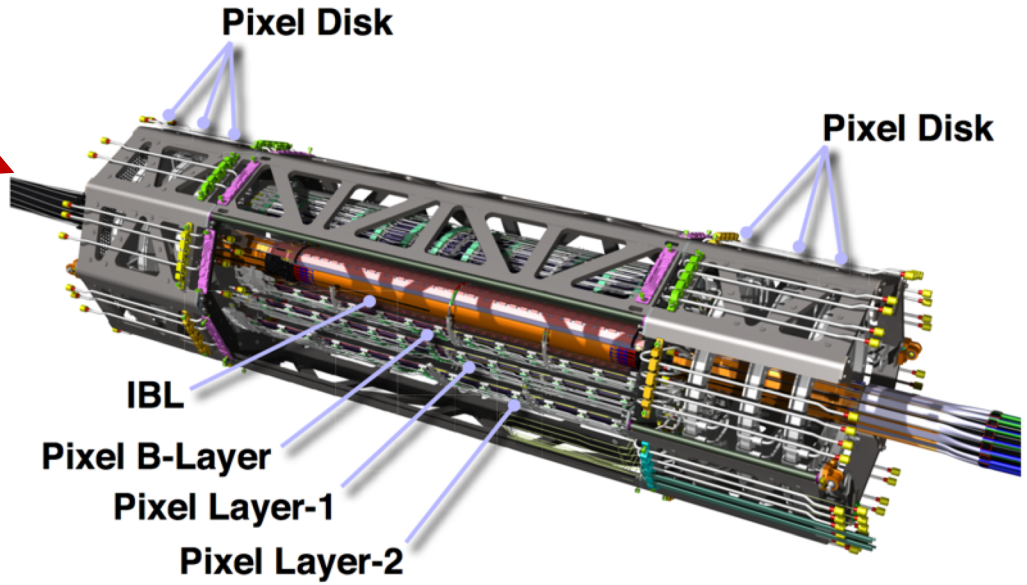
ATLAS Pixel Detector



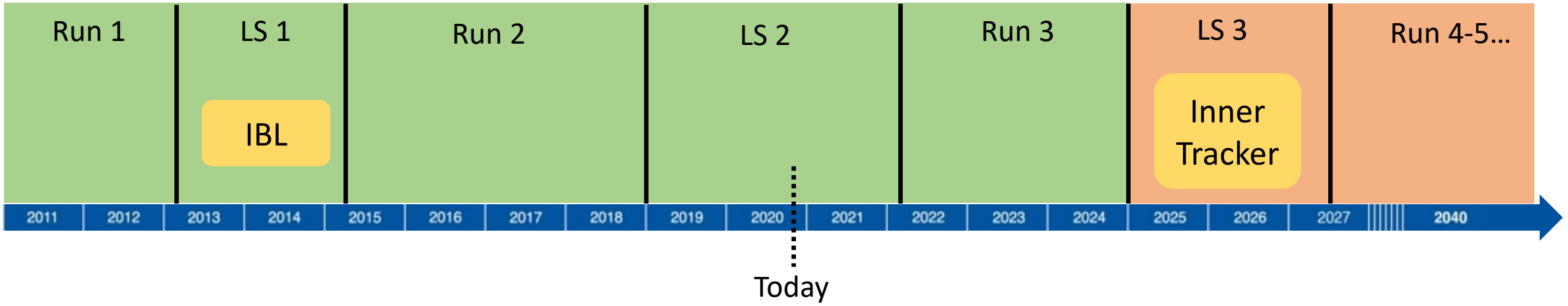


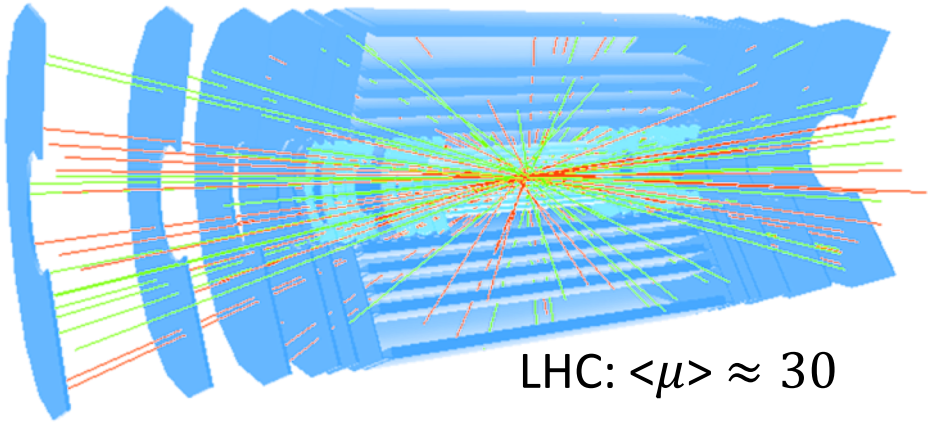
ATLAS Pixel Detector

Upgrades of the ATLAS Pixel Detector

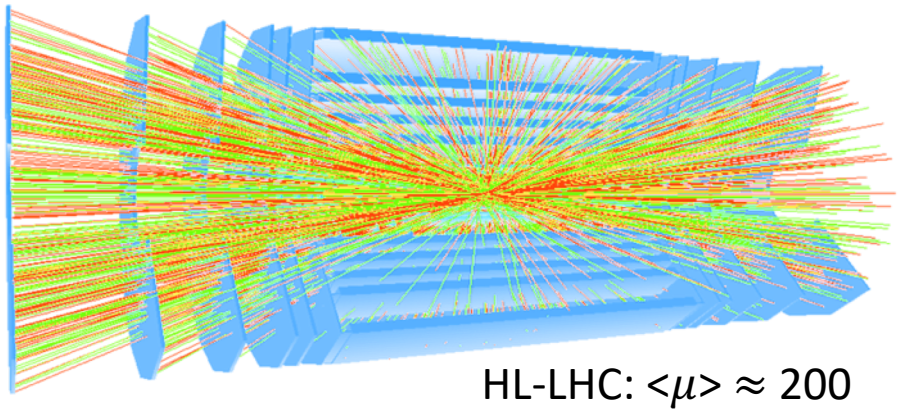
LHC

HL-LHC





LHC: $\langle\mu\rangle \approx 30$

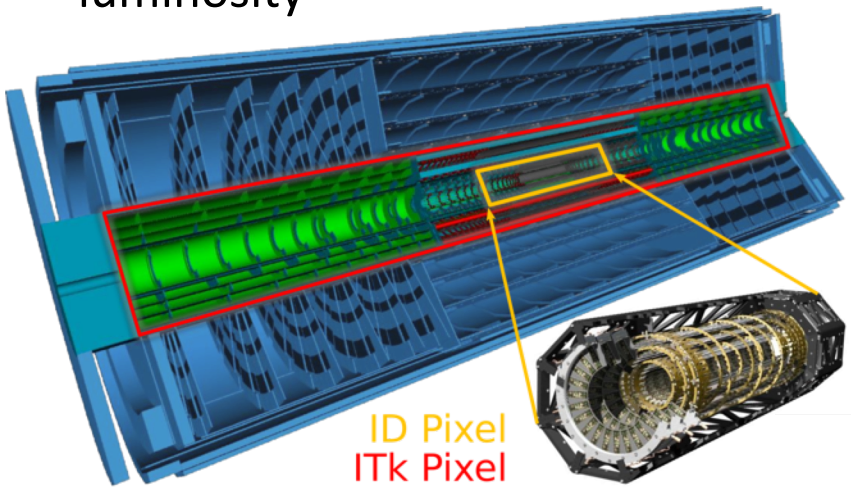


HL-LHC: $\langle\mu\rangle \approx 200$

Inner Tracker (ITk)

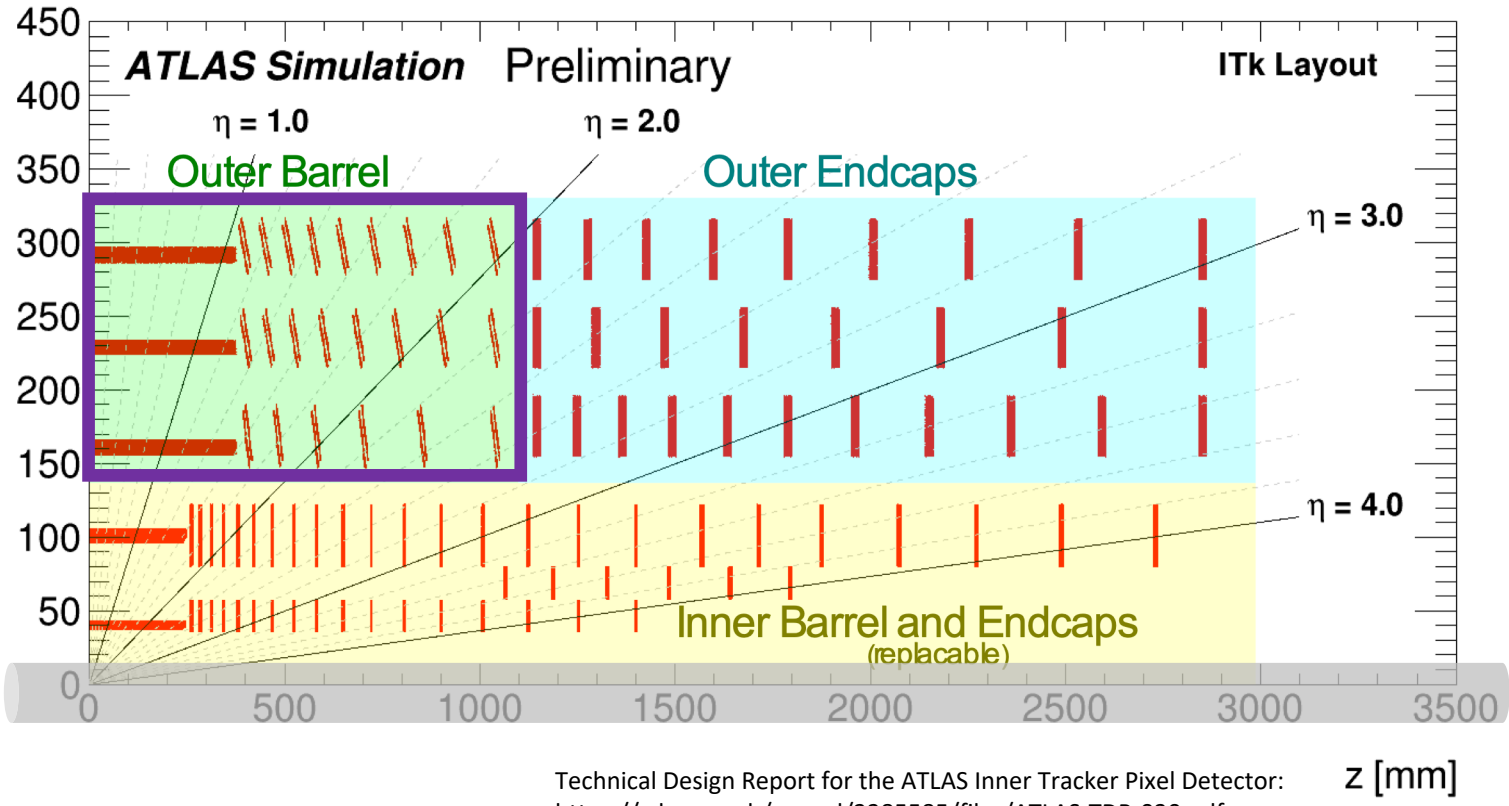
HL-LHC (Phase-II) Upgrade

- Current tracking detector (ID) will be replaced by an all silicon tracker, the Inner Tracker (ITk)
- ITk consists of a pixel and a strip subdetector
- Requires novel silicon modules, powering and data transmission schemes to cope with the challenges of the increased luminosity



Most Important challenges for pixel detector:

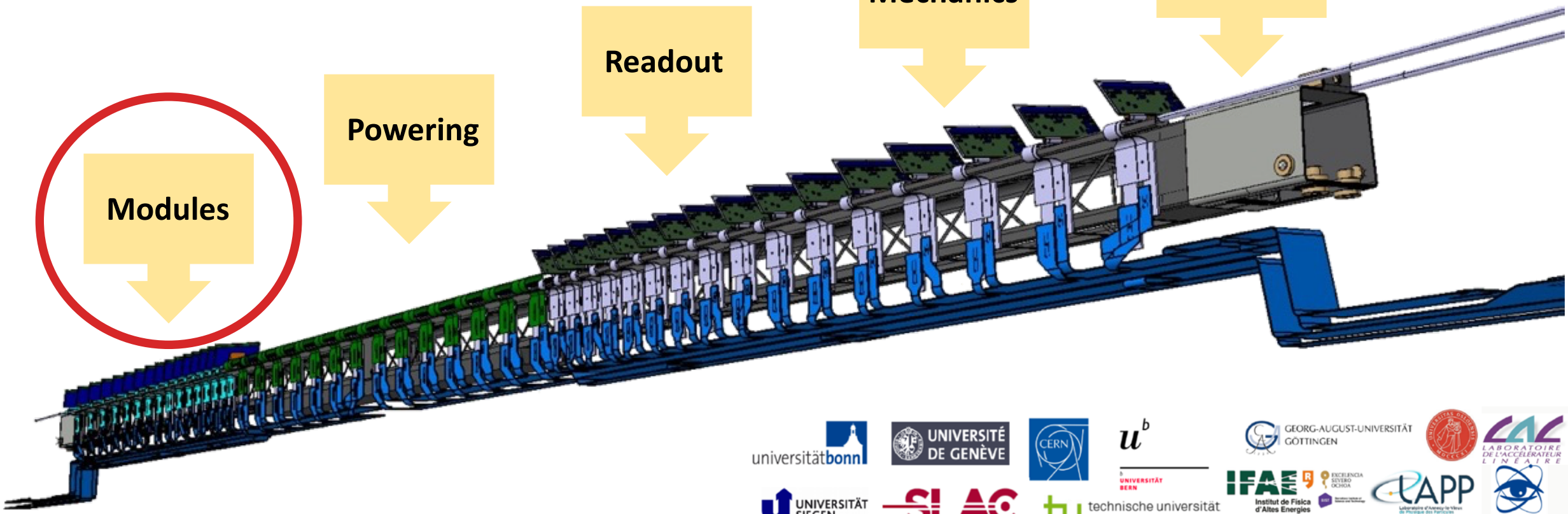
- low occupancy and high data rates
- radiation hardness



Technical Design Report for the ATLAS Inner Tracker Pixel Detector:
https://cds.cern.ch/record/2285585/files/ATLAS-TDR-030.pdf

Outer Barrel Demonstrator

Design and system verification of outer barrel layers

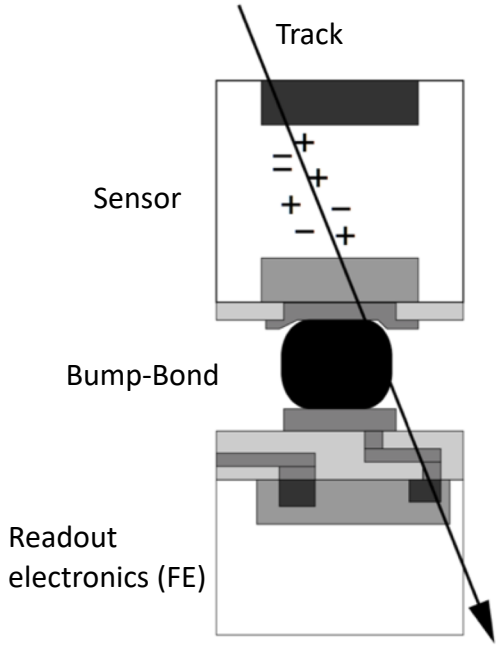


In total 46 pixel modules needed

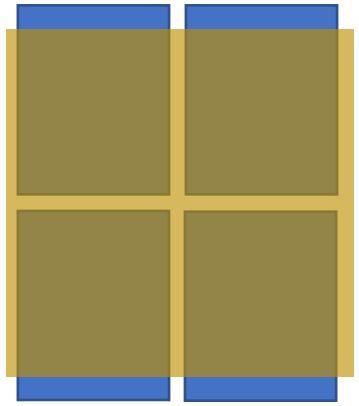
Module Production Steps

“Bare” Module

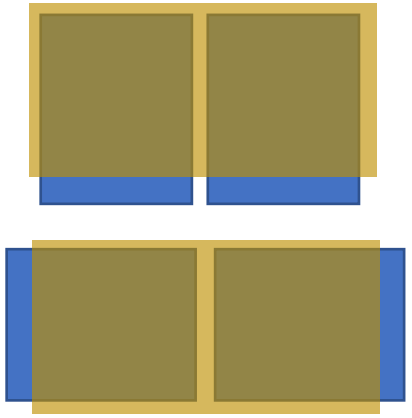
- Planar pixel modules with FE-I4b chips (Hybrid)
- Technology used for IBL
- 336 x 80 pixel, 50 x 250 µm²
- Each pixel of sensor is connected with one channel of FE via Bump-Bond (flip chiping)



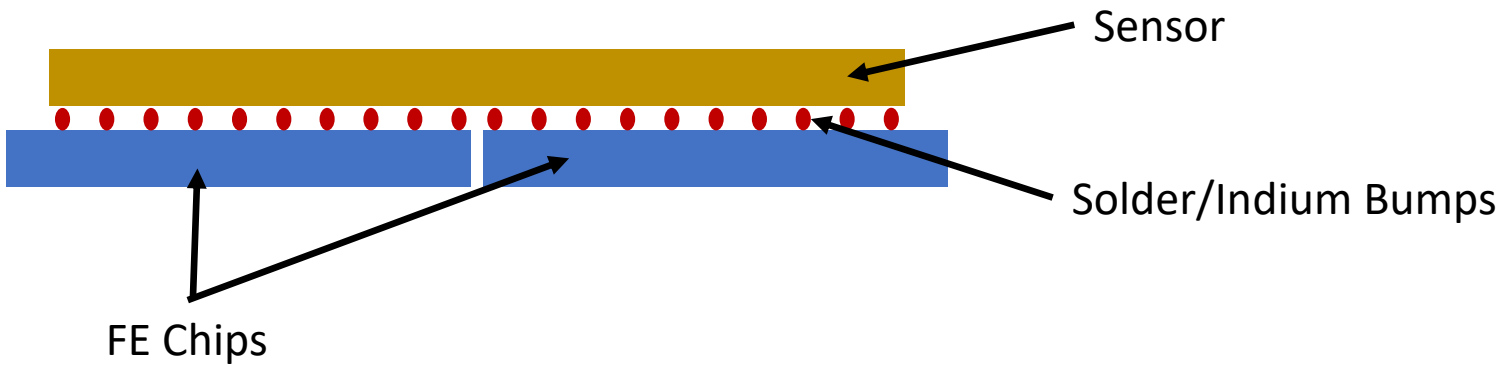
Pixel Detectors for Charged Particles, N. Wermes, arXiv:0811.4577



Quad Chip Module



Dual Chip Module



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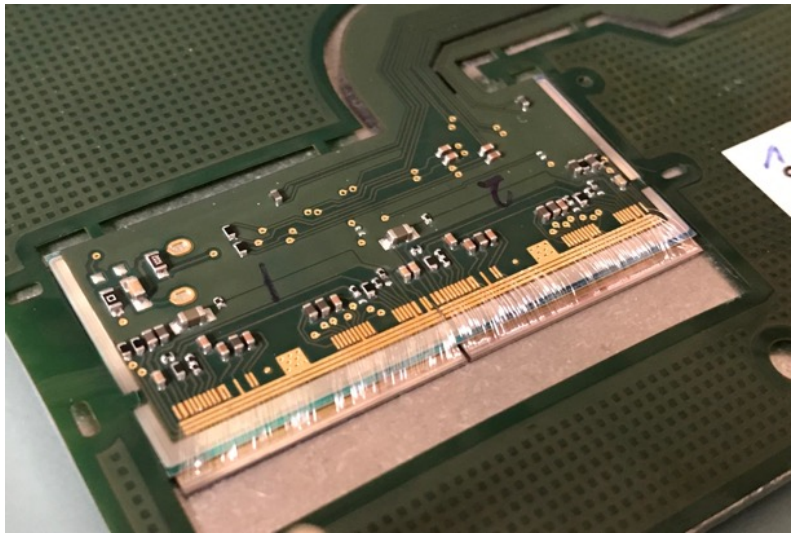
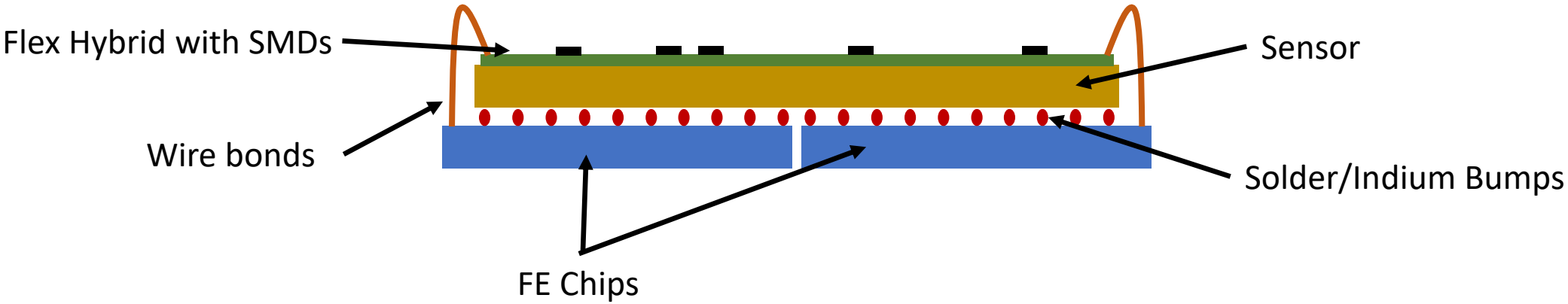
“Dressed” Module

- Attaching flip chipped bare module to module flex
- Using UHU Endfest 300 epoxy for physical attachment of the components
- Wirebonding for electrical connection between flex and FEs pads

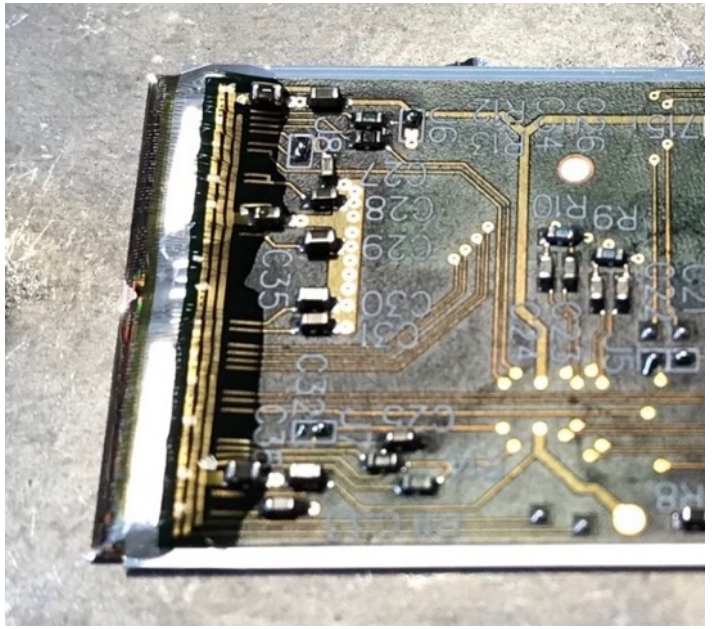


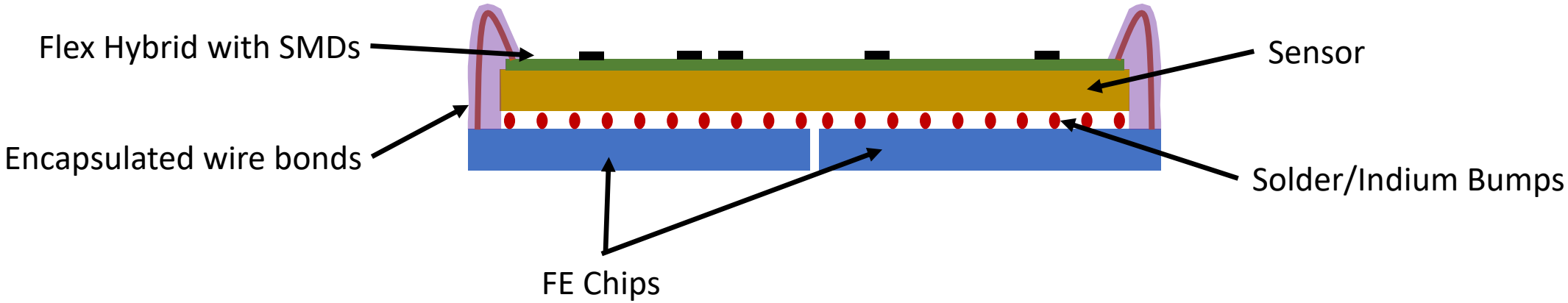


Module Production Steps

“Potted” Module

- Encapsulation of fragile wirebonds
- Manual and automatic procedure used
- Using Sylgard 186 Silicone Elastomer
- Study ongoing for alternative (combination of parylene and mechanical protection)

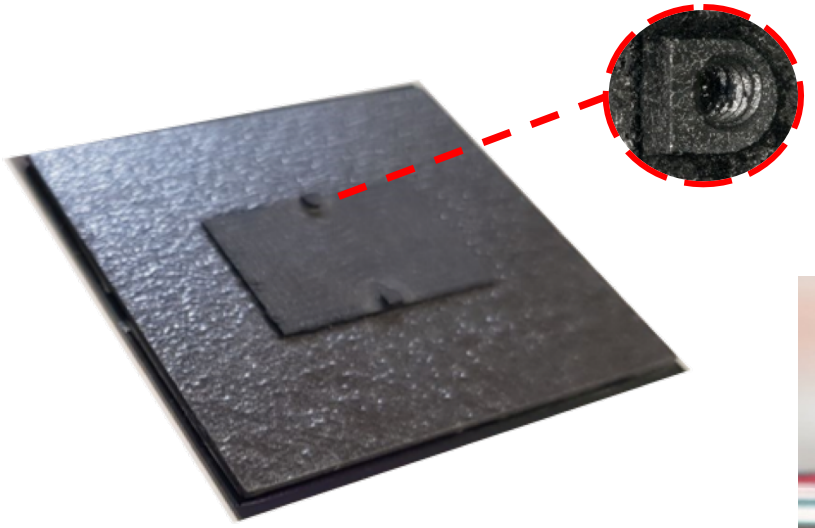


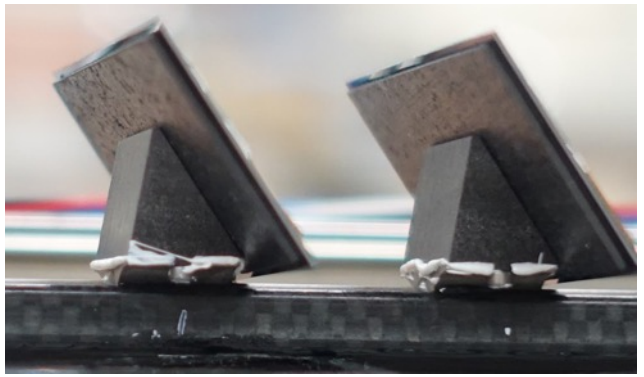


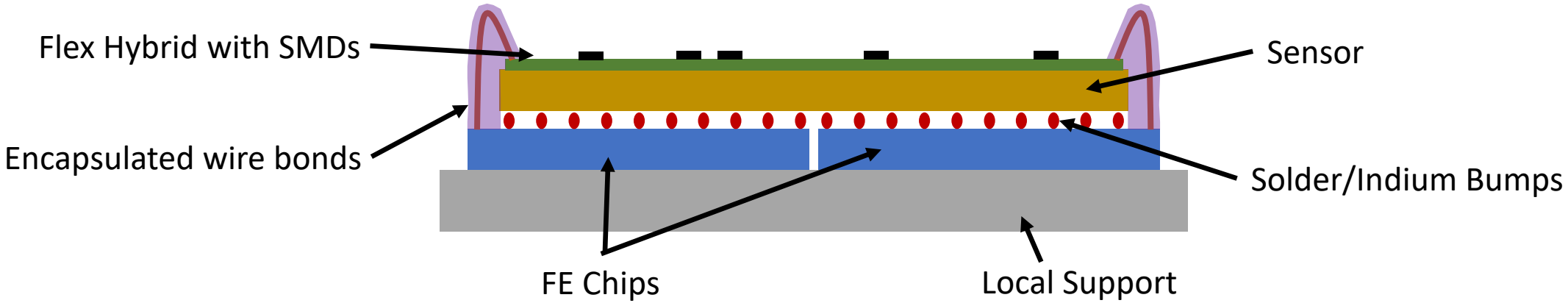
Module Production Steps

“On Cell” Module

- Light graphene interface to connect module with carbon support
- Used for mounting and cooling
- Good thermal contact
- Flat and inclined cells

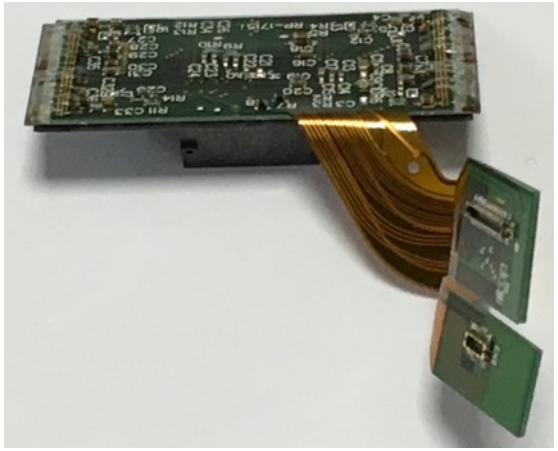




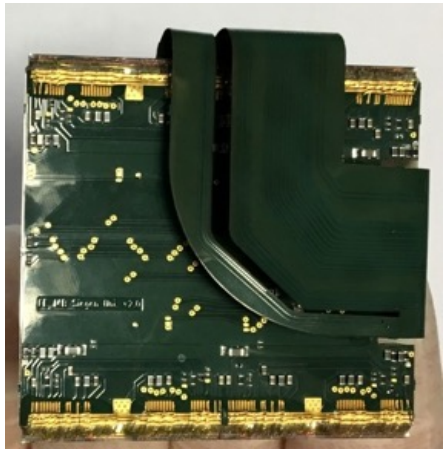


Module Production Steps

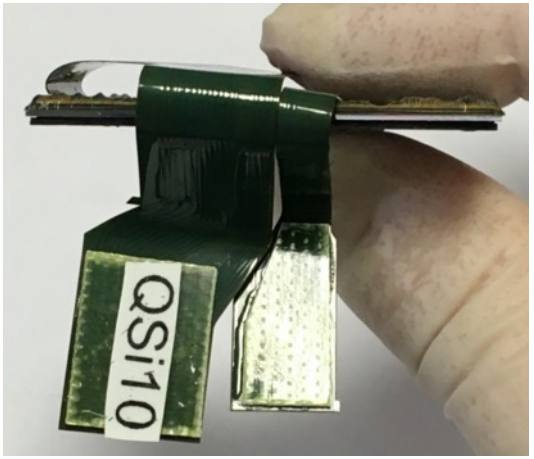
“Bent” Module



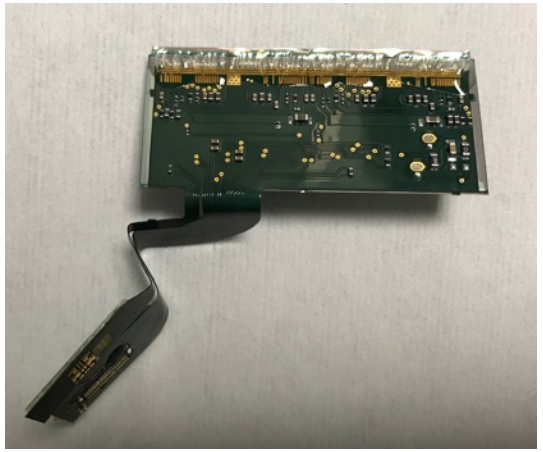
A-side Dual



Quad

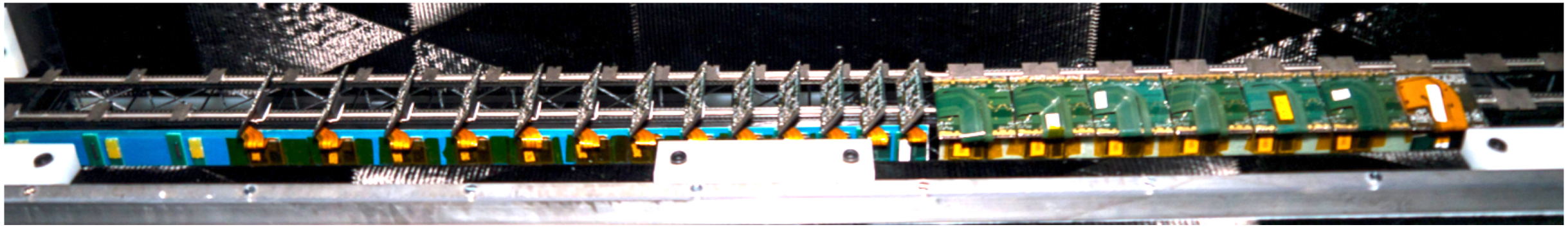


Quad (side view)



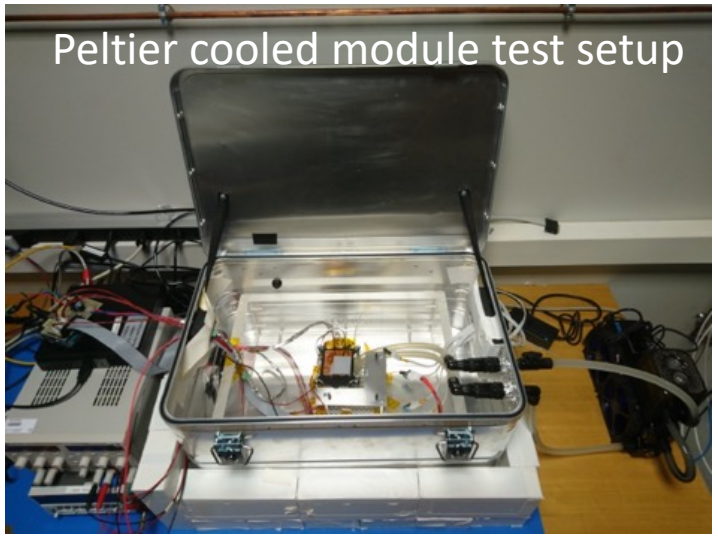
C-side Dual

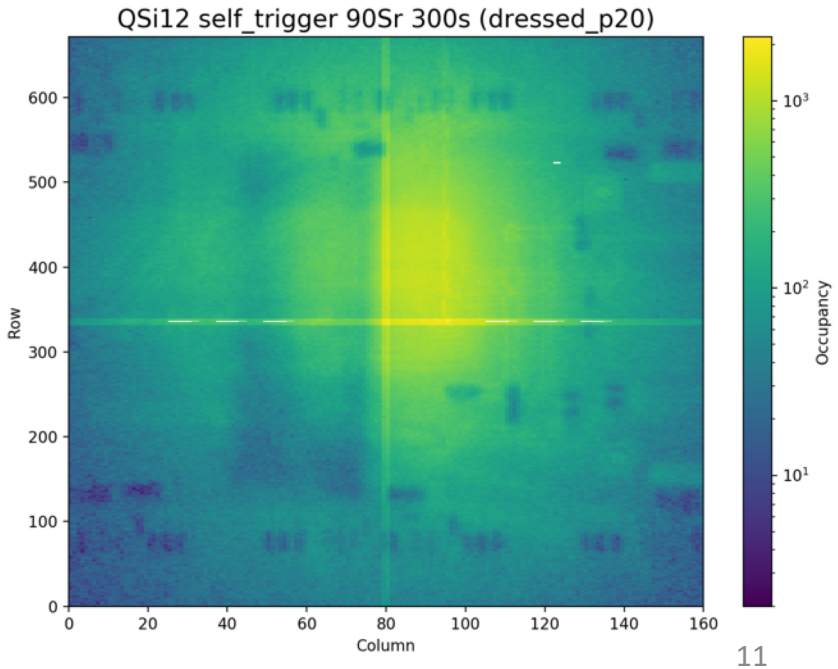
“Integrated” Module



Module Testing

1. **Visual inspection**
2. **IV curve**
3. **Tuning**
4. **Scans:**
   - Digital Scan, Analog Scan, Threshold Scan, Stuck Pixel Scan, Noise Occupancy Tuning, Hot Pixel Tuning
   - Source Scan with ^{90}Sr source





- Modules are operated in a controlled environment :
  - Dry air
  - Cooling
- Modules powered in constant current mode

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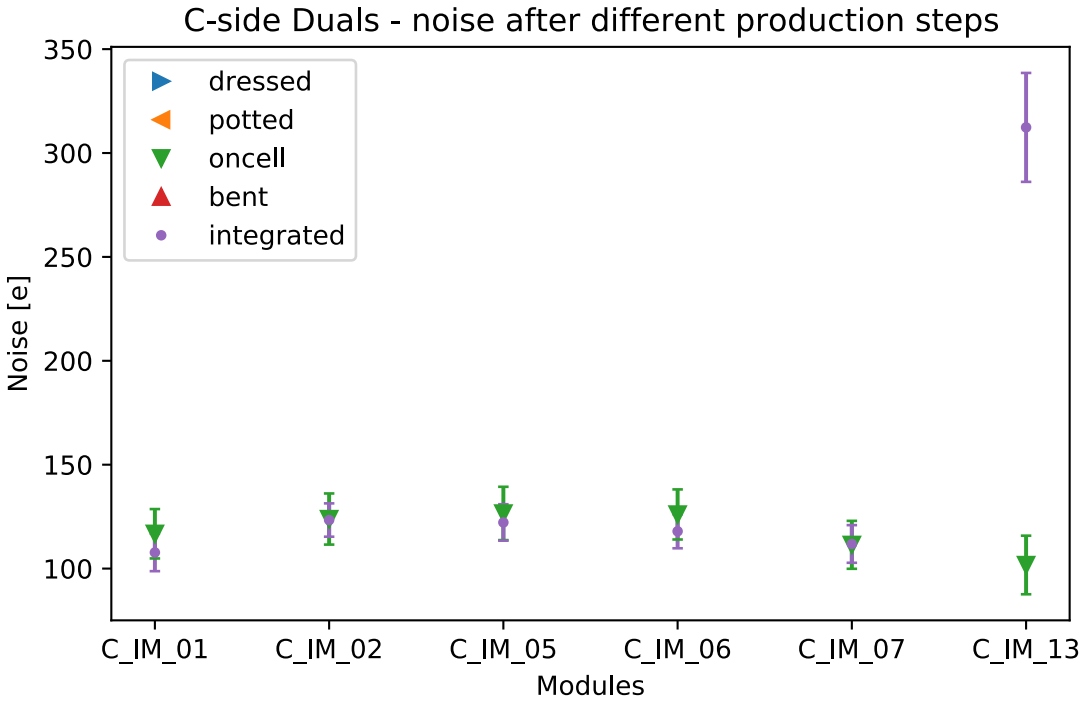
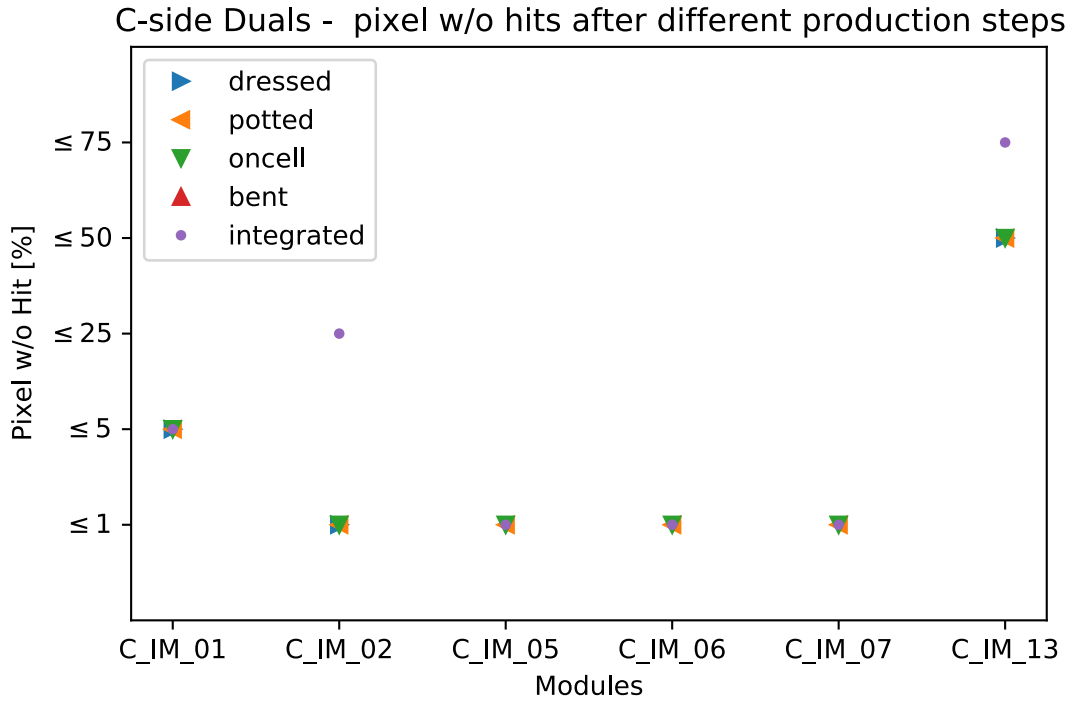
Electrical Test Results



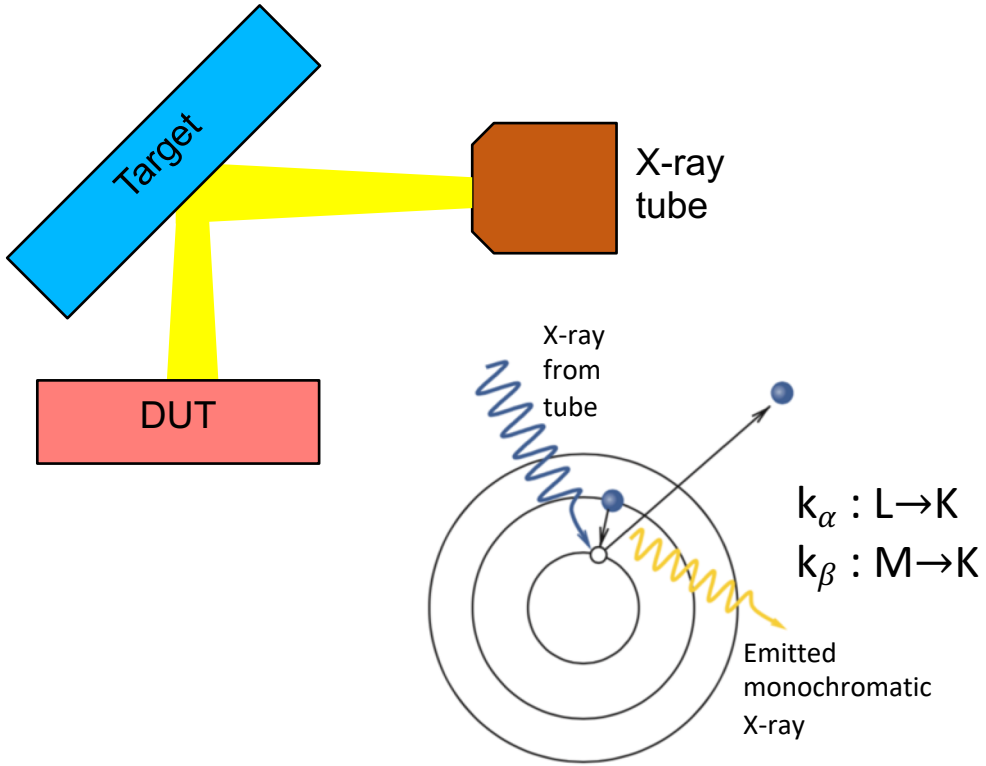


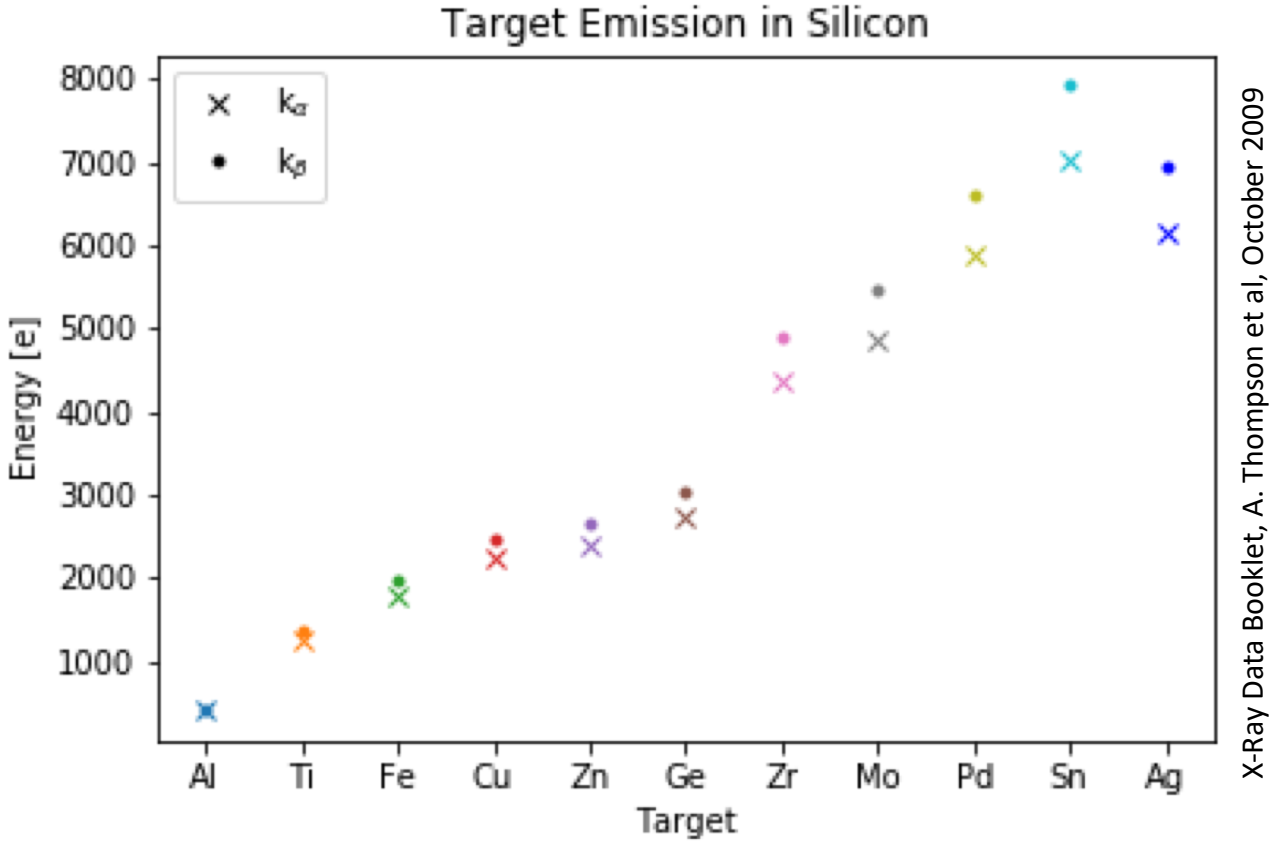
- Systematic study showing good results
- In total 40 Quads and 48 Duals were produced and tested

Characterization of RD53A pixel modules using X-Ray Fluorescence

X-Ray Fluorescence Method

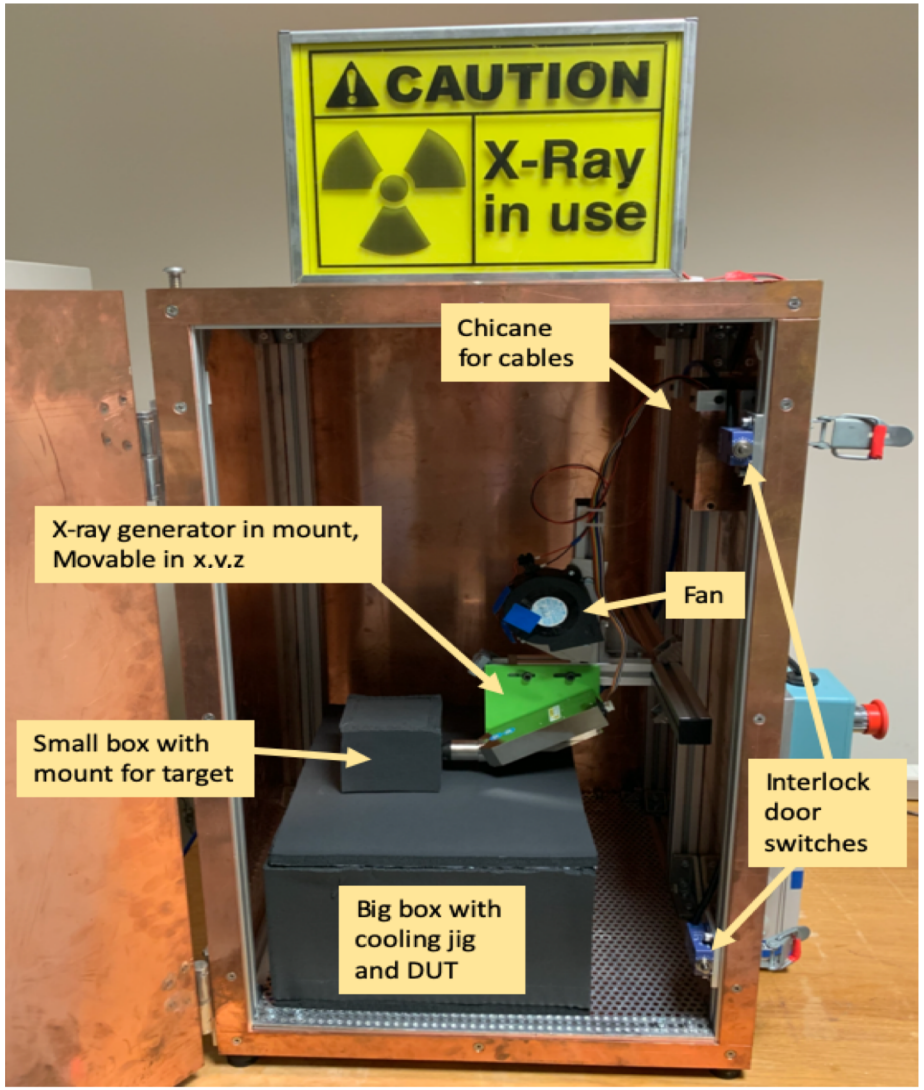
- Method to calibrate and study the linearity of response of new pixel modules in the lab
- Allows measurement of charge spectra and energy resolution

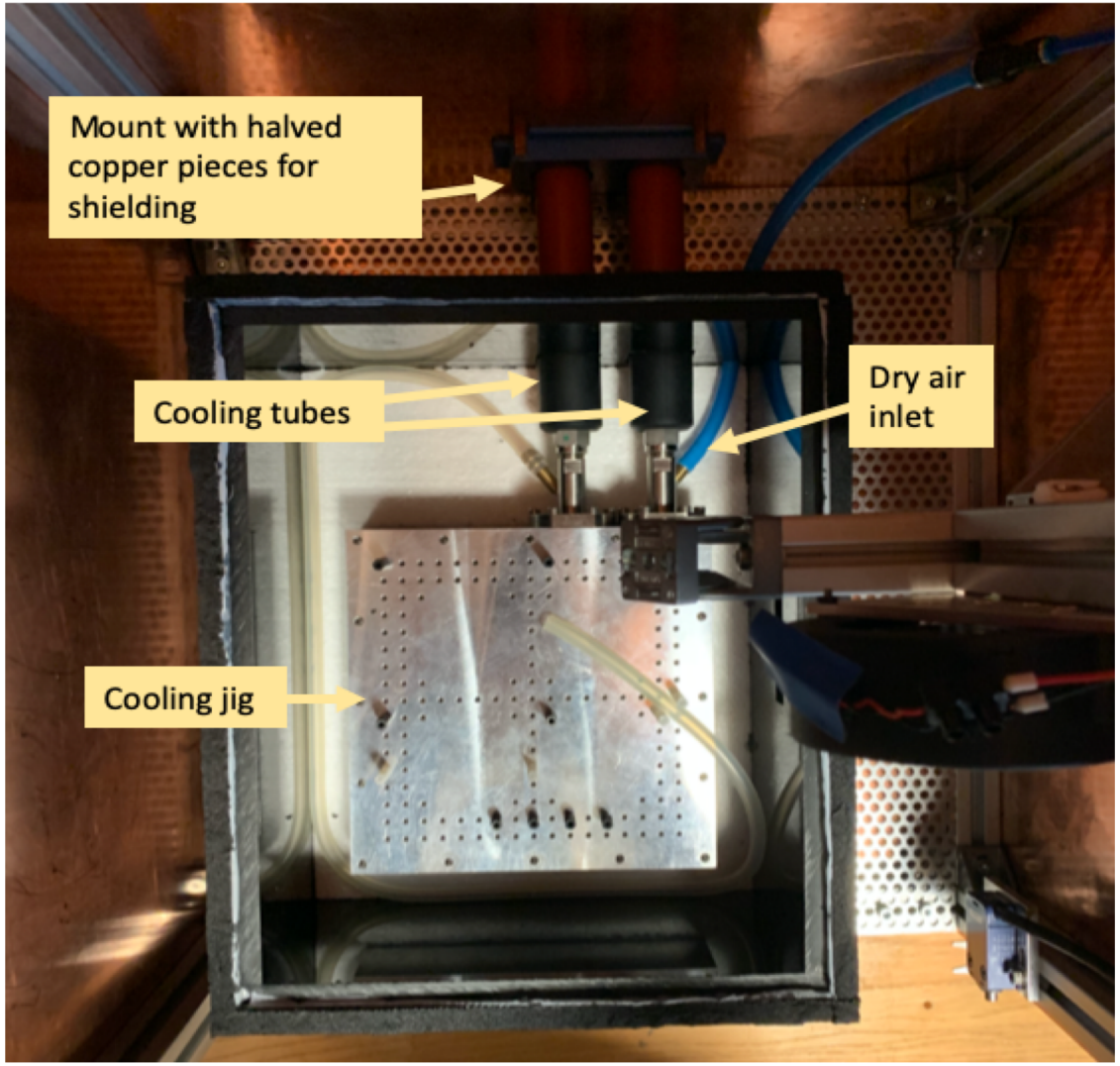




- **Targets:** Aluminum (Al), Titanium (Ti), Iron (Fe), Copper (Cu), Zinc (Zn), Germanium (Ge), Zirconium (Zr), Molybdenum (Mo), Palladium (Pd) and Tin (Sn)
- Amptek Mini-X2 X-ray tube (50kV, 200 μA, 4W, Ag)

X-Ray Fluorescence Setup





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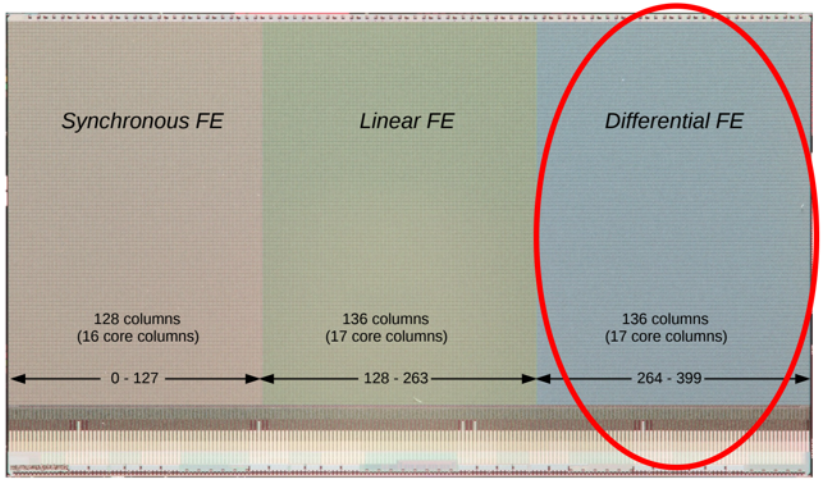
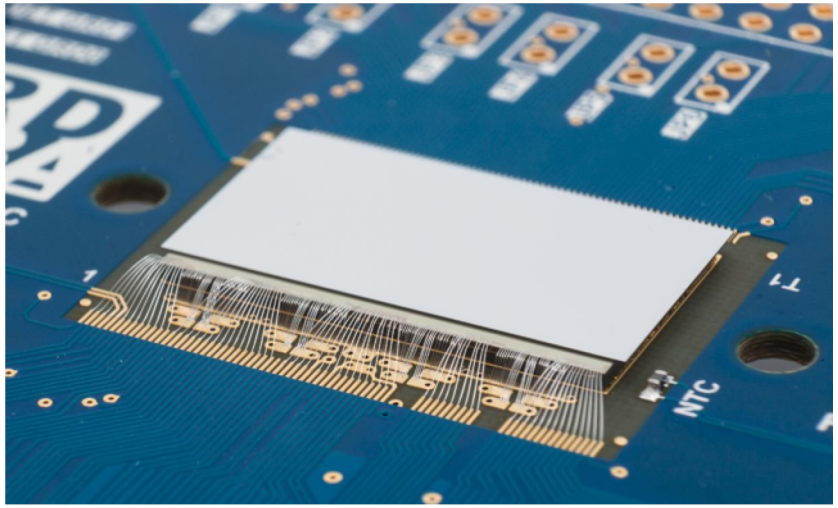
RD53A Module

- Future readout chip for ATLAS and CMS pixel detectors
- Developed by RD53 collaboration
- RD53A (half size chip): 400 x 192 pixel, 50 x 50 μm^2
- FE separated in 3 parts with different analog flavors
- ATLAS has chosen Differential FE

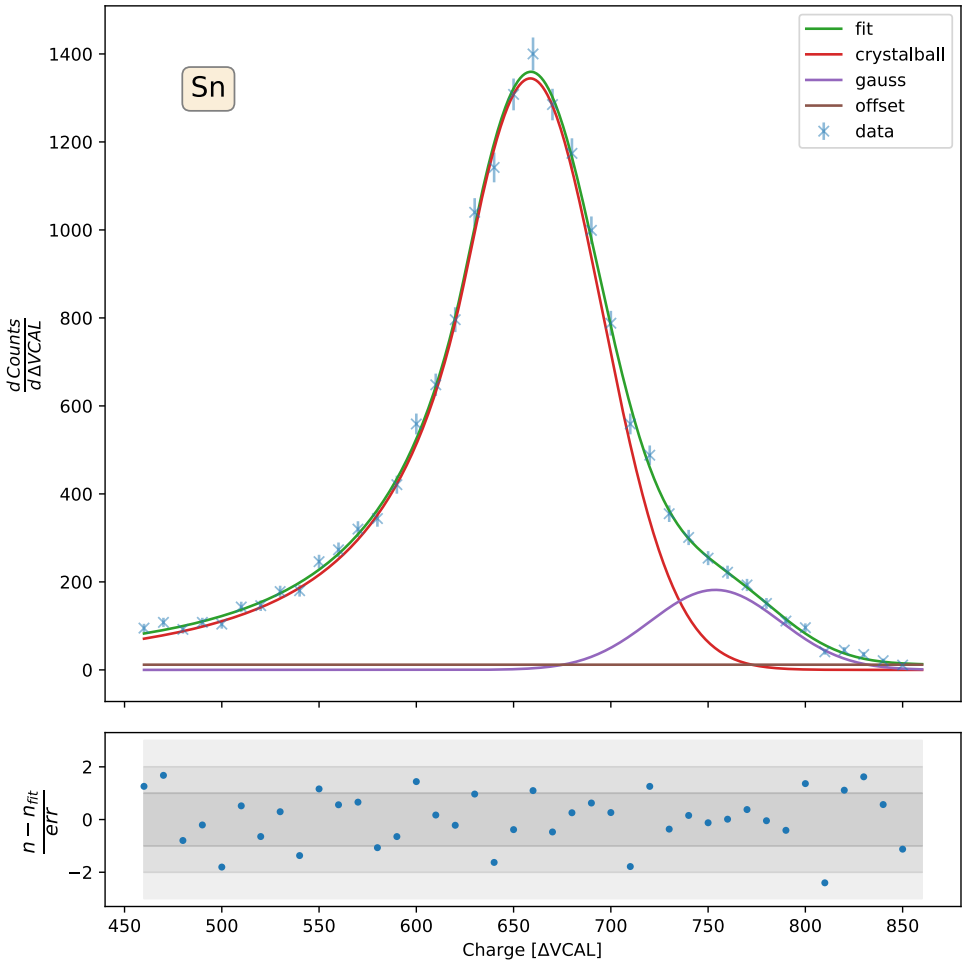


Technical Data:
- High hit rate: 3GHz/cm^2 (FE-I4:400 MHz/cm^2)
- High trigger rate: 1 MHz with 12.8 µs latency
- Data rate up to 5.12 Gbit/s per chip
- Low threshold ~600e
- 500 Mrad radiation tolerance
- Low power: ~4µA/pixel (analog/digital)

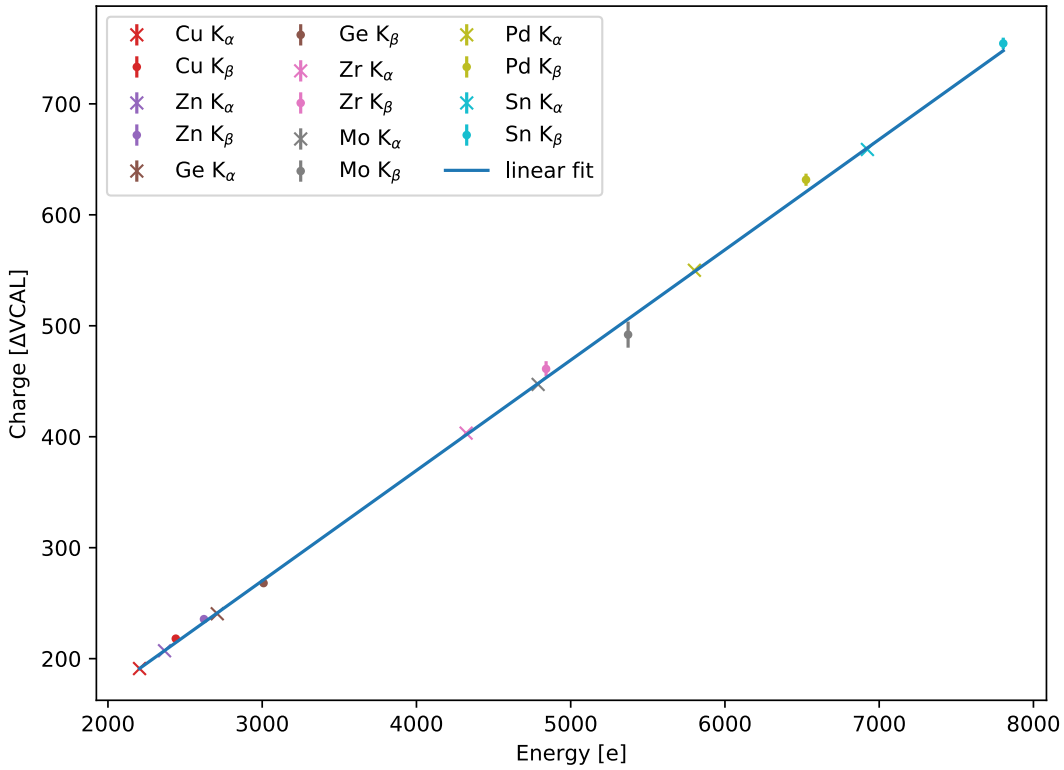


Results of Differential FE

Tuning: 1000e Threshold, 10ToT@8ke



fit = crystalball(k_α) + gauss(k_β) + offset



- ΔV_{CAL} is internal energy unit of RD53A chip
- Energy [e] = 10.06 e/ΔV_{CAL} * Charge [ΔV_{CAL}] + 282.84 e

Summary and Outlook

Summary:

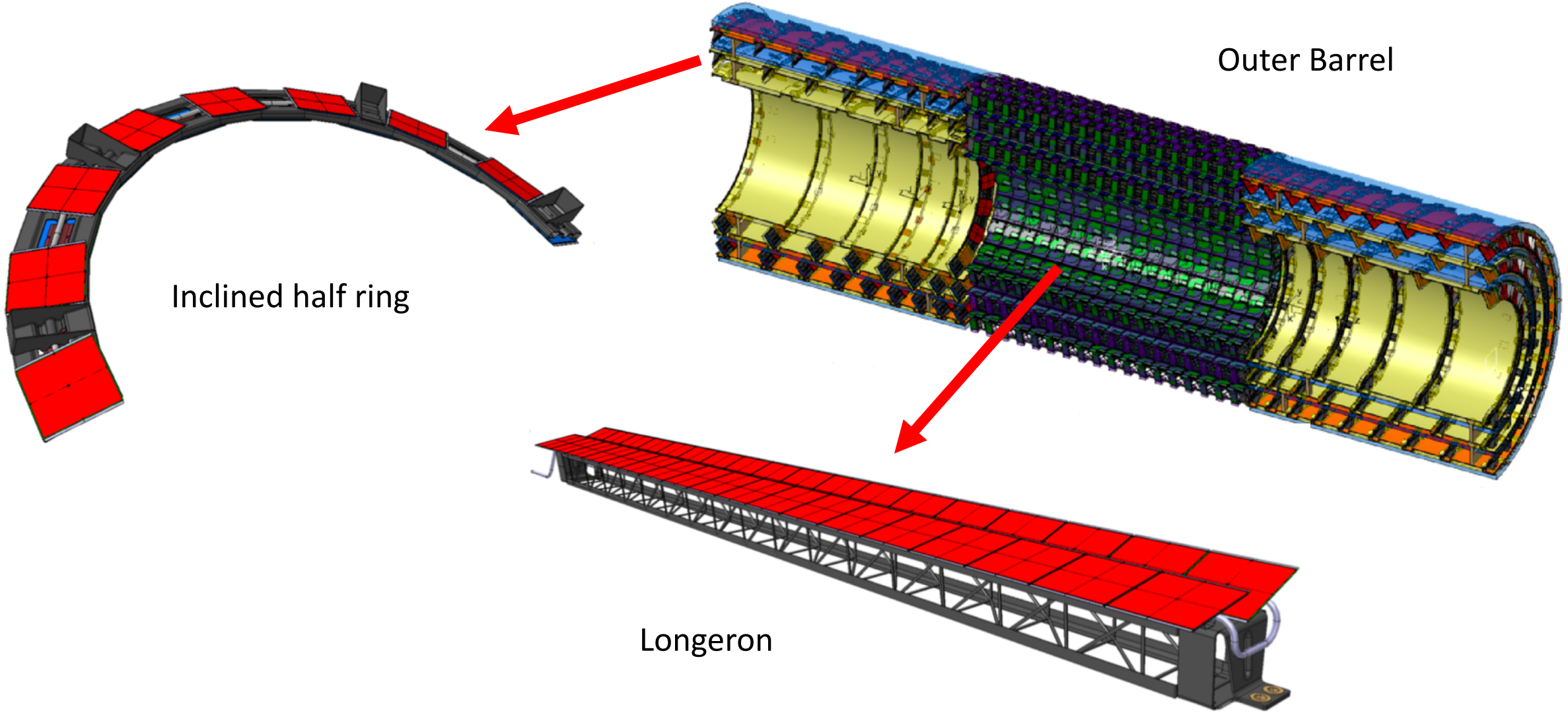
- Systematic investigation of new pixel modules for the upgrade of the pixel detector of the ATLAS experiment
- Assembly and testing of many modules through production flow
- Collected experience and lessons learnt in distributed production flow and resulted in optimization of all production steps
- Large variations in noise and number of pixel w/o hit due to the production steps have not been observed
-
- For further investigation of new pixel modules built and commissioned X-ray Fluorescence setup which can be operated at temperatures low as -35 °C
- Energy calibration conducted for unirradiated RD53A pixel module

Outlook:

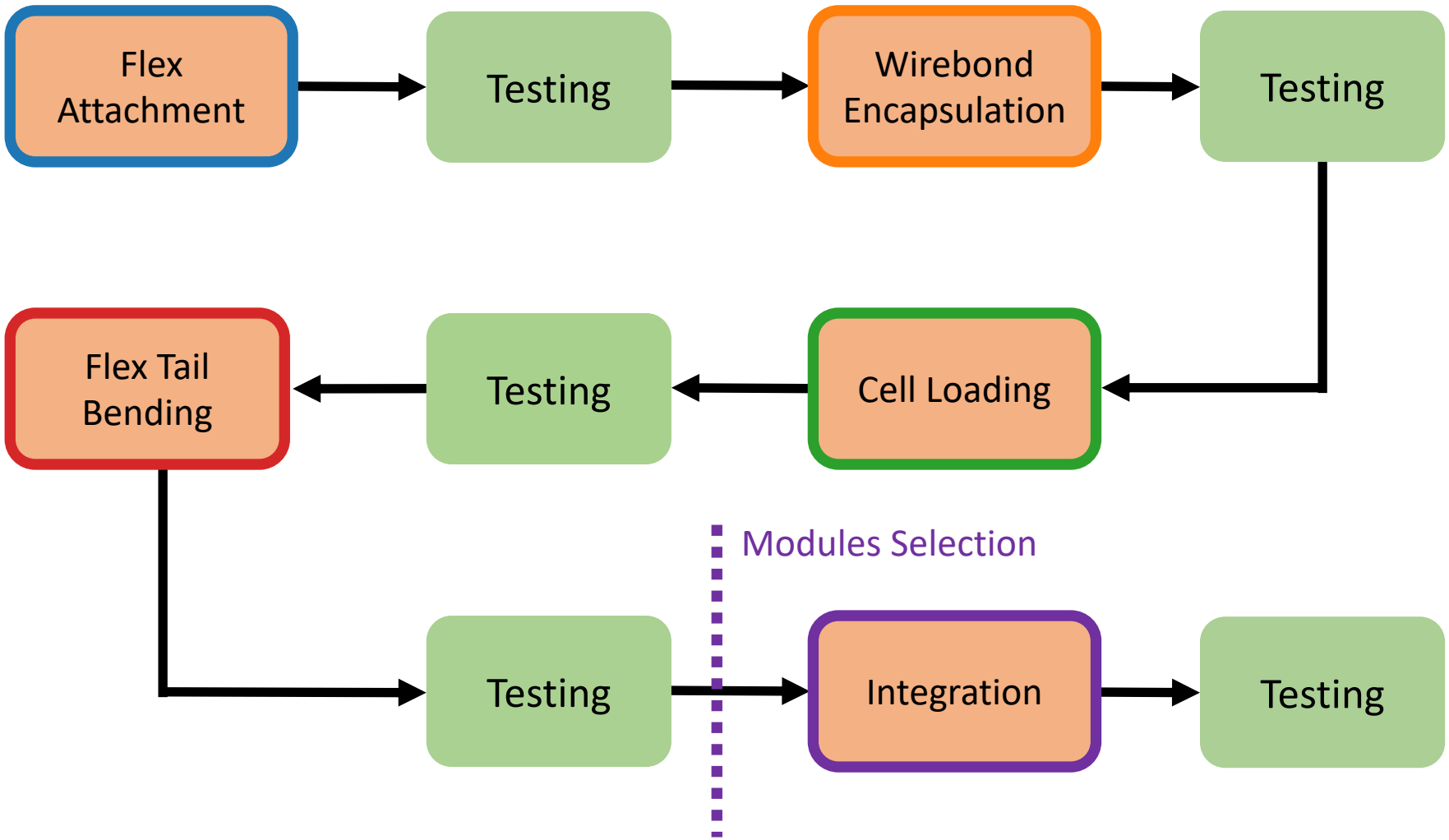
- Energy calibration of irradiated RD53A pixel modules and new pixel modules using X-Ray Fluorescence

Backup

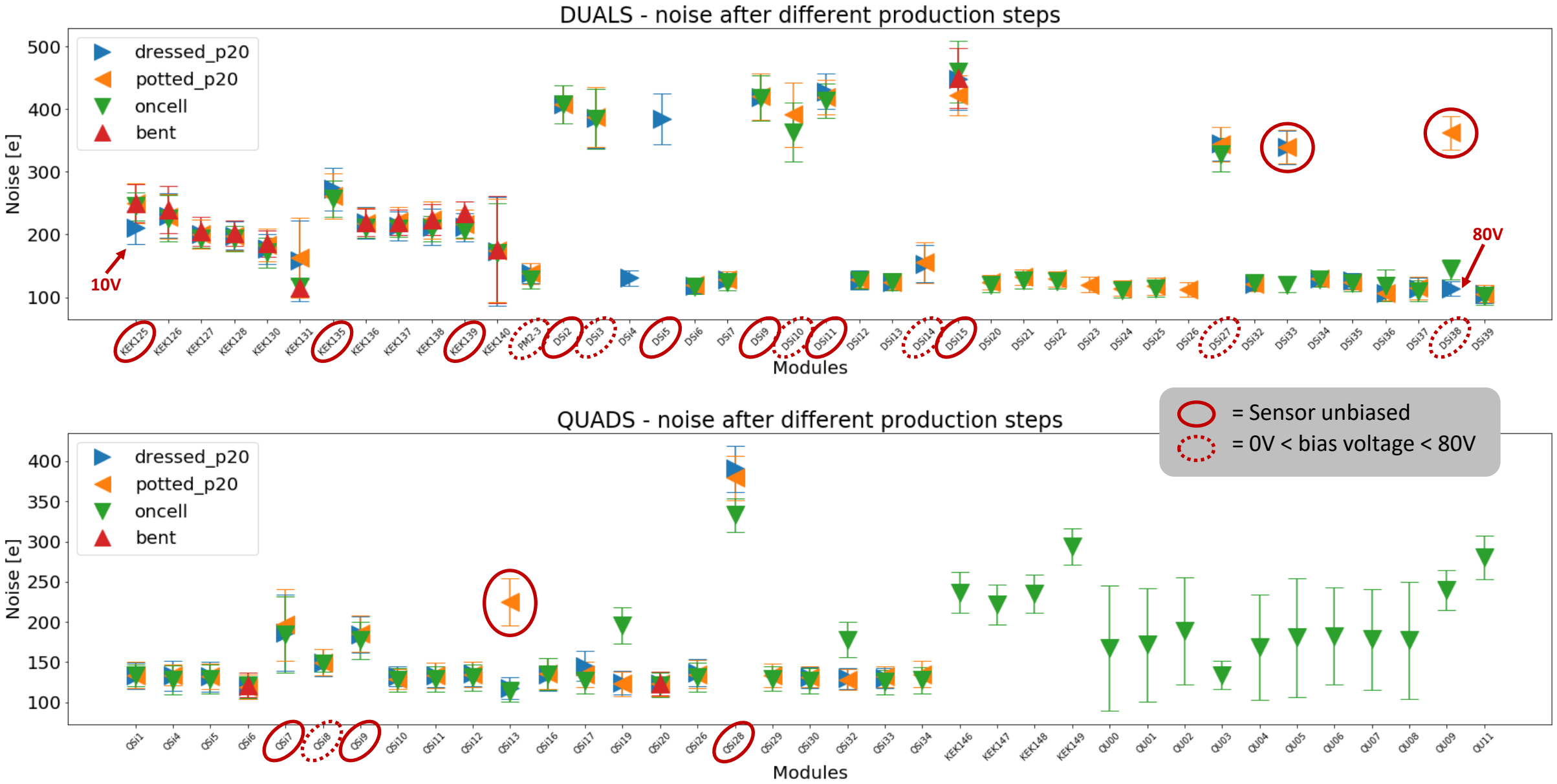
Outer Barrel System



Path of the Modules

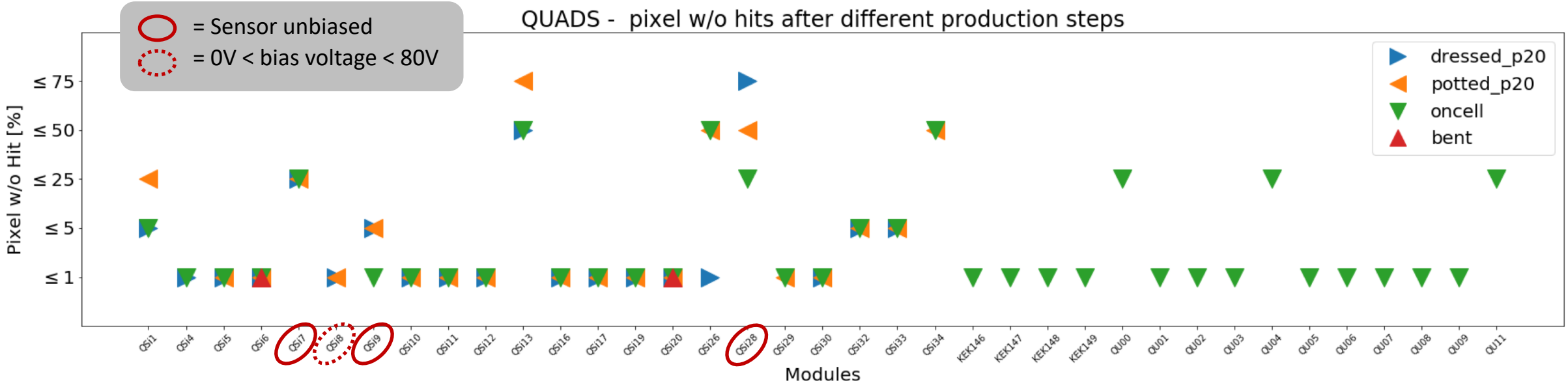


Noise after different production steps

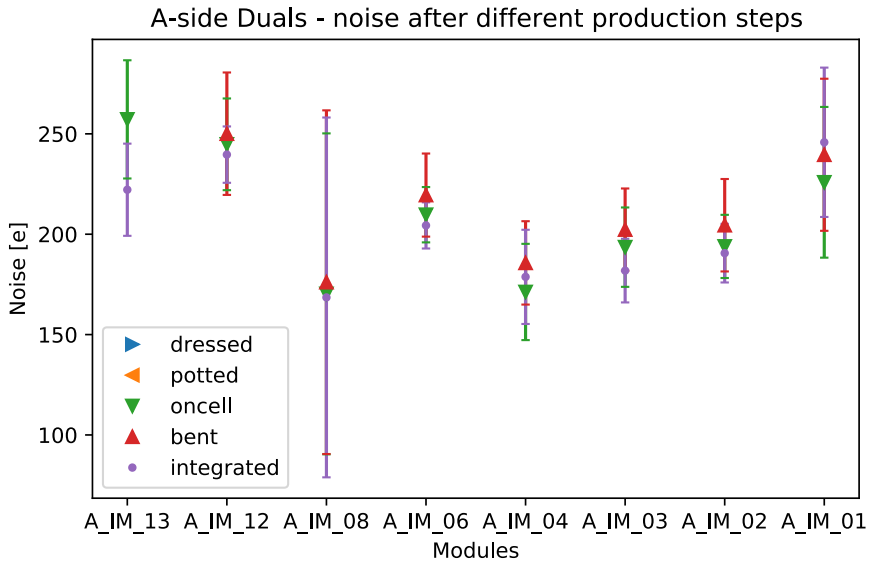


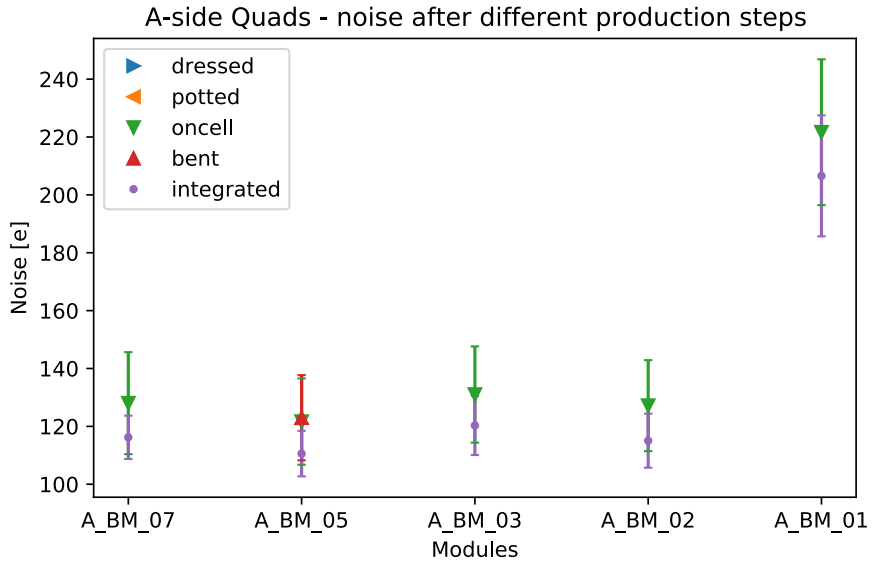
Pixel w/o hits after different production steps

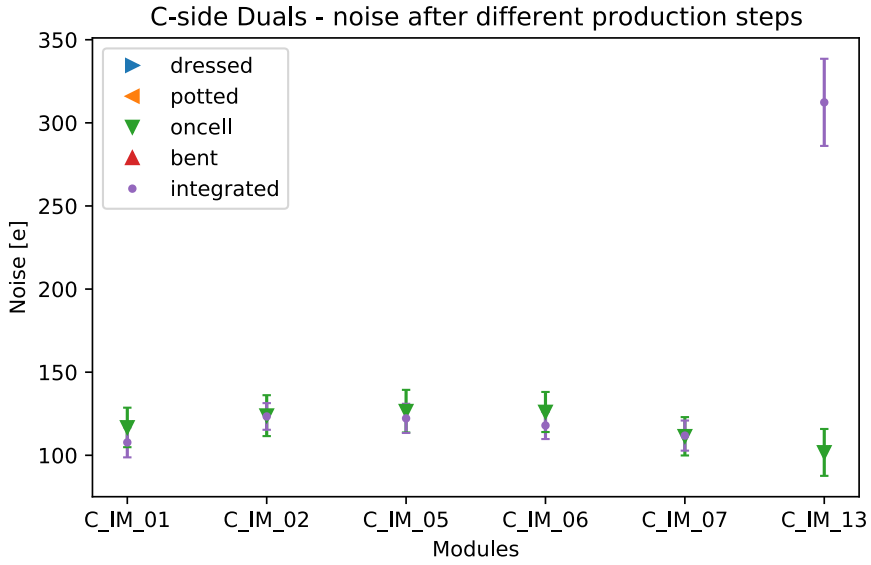
= Sensor unbiased
= 0V < bias voltage < 80V

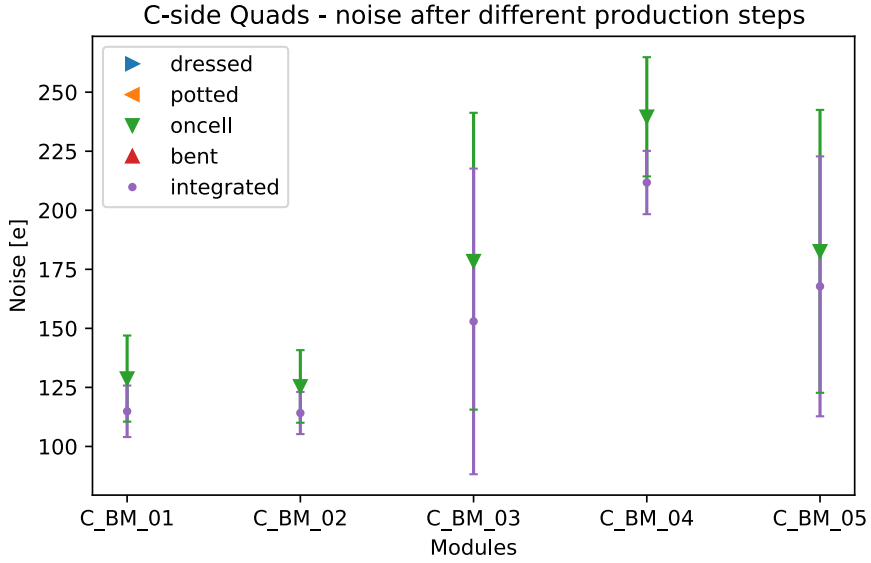


Noise after different production steps









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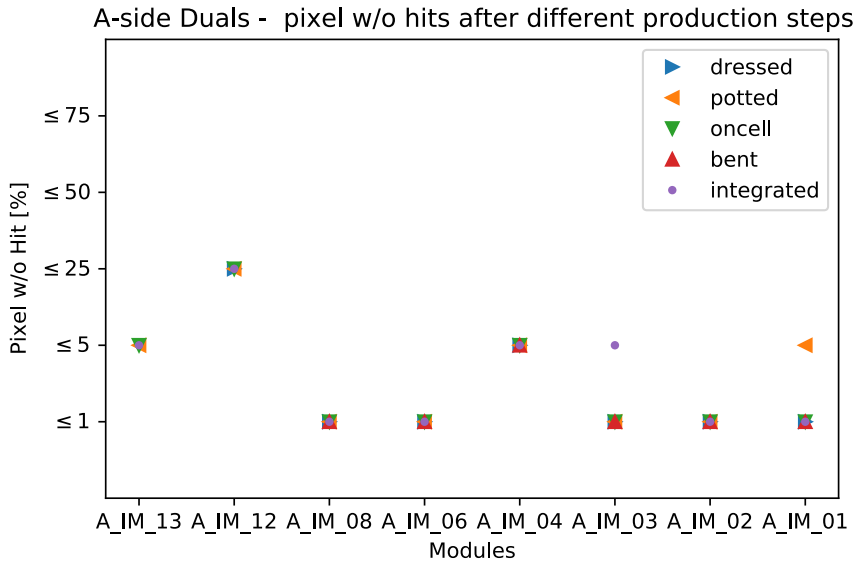
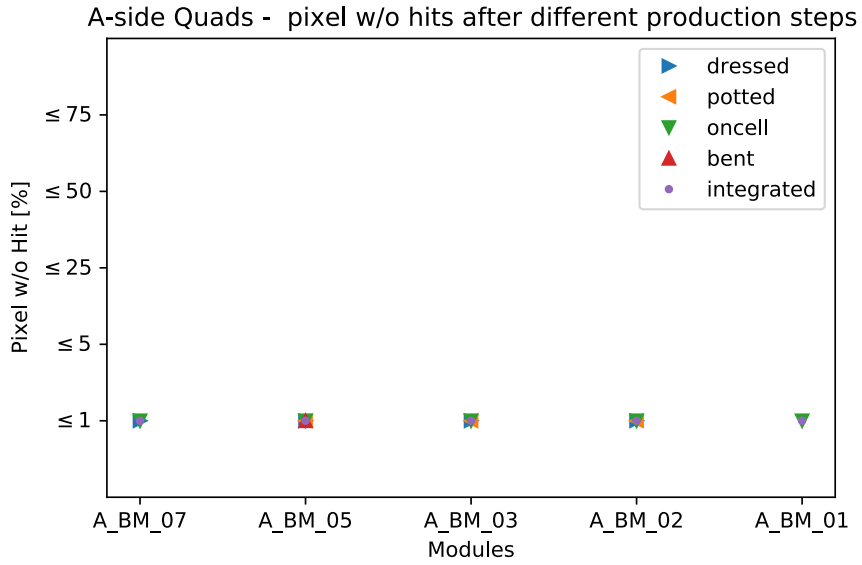
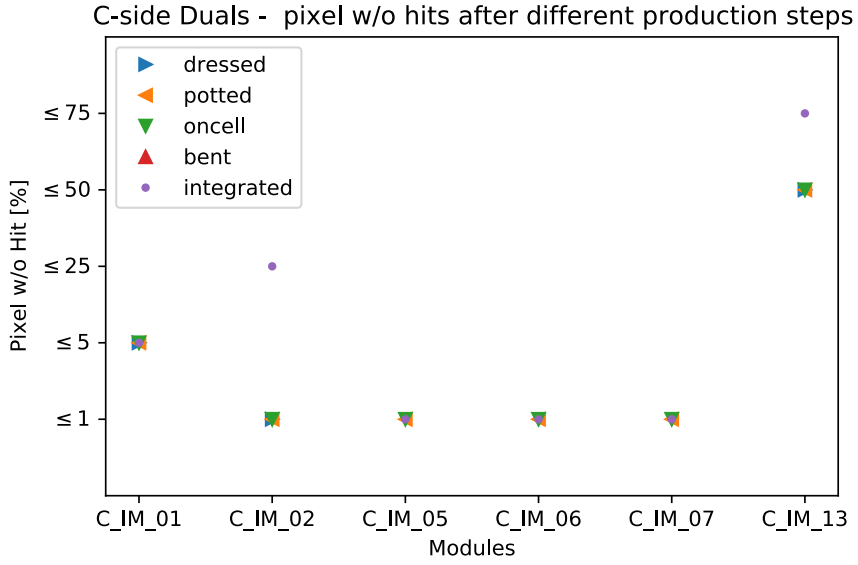
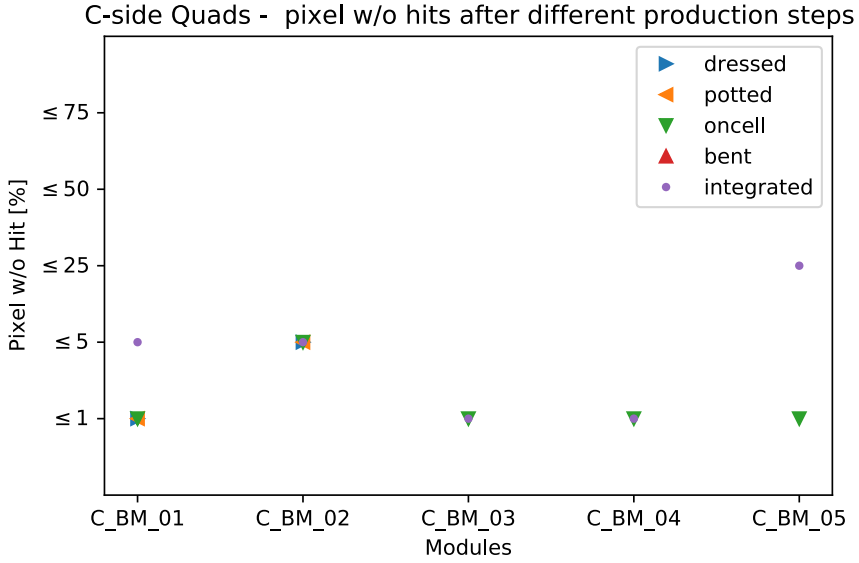
Pixel w/o hits after different production steps









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